

6367255 MOTOROLA SC (DIODES/OPTO)

34C 38147 D

SILICON THYRISTOR DIE (continued)

T-25-13

DIE NO. 2C2326
LINE SOURCE — DTL638



SCR-Silicon Controlled Rectifier

Device assembled from this die type are similar to the following device types:

- | | |
|--------|------------------|
| 2N2322 | 2N4216 |
| 2N2323 | 2N4217 |
| 2N2324 | 2N4218 |
| 2N2325 | 2N4219 |
| 2N2326 | 2N6236 |
| 2N2327 | 2N6237 |
| 2N2328 | 2N6238 |
| 2N2329 | 2N6239 |
| 2N4212 | 2N6240 |
| 2N4213 | 2N6241 |
| 2N4214 | C106A series |
| 2N4215 | MCR106-1 series |
| | MCR1906-1 series |

70 mils

Backside: Anode

METALLIZATION —
 Top Al
 Back Au

GOLD THICKNESS 9000 Å

DIE THICKNESS 8 ± 2 mils

BONDING PAD SIZE —
 Cathode 35 x 35 mils
 Gate 13 x 18 mils

11

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, Note 1, $R_{GK} = 1.0 \text{ k}\Omega$)

Parameter	Test Conditions	Min	Max	Unit
I_{DRM}	$V_D = 200 \text{ Vdc}$	—	20	μAdc
I_{RRM}	$V_R = 200 \text{ Vdc}$	—	20	μAdc
I_{GT}	$V_D = 12 \text{ Vdc}$, $R_L = 24 \Omega$	—	200	μAdc
I_H	$V_D = 12 \text{ Vdc}$, $I_{TM} = 200 \text{ mAdc}$	—	5.0	mAdc
V_{GT}	$V_D = 12 \text{ Vdc}$, $R_L = 24\Omega$, $R_{GK} = 1.0 \text{ k}\Omega$	—	1.5	Vdc

- NOTES:
1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 2. Detailed device characteristics are available from your Motorola sales representative.